

What is claimed is:

1. A semiconductor device comprising:
 - a substrate;
 - a first insulator layer formed on the substrate;
 - a first conductive layer formed on the first insulator layer;
 - a second insulator layer formed on the first conductive layer;
 - a second conductive layer formed on the second insulator layer;
 - sidewalls each formed on a side face of a hole vertically extended through the second insulator layer;
 - and
 - fuses each formed of a conductive material that buries a space defined inside the sidewall, said fuse having a lower end connected to the first conductive layer and an upper end connected to the second conductive layer.
2. A semiconductor device according to claim 1, wherein the fuses and the second conductive layer are formed of the same material.
3. A semiconductor device according to claim 1, wherein the sidewall includes a first layer formed on an inner surface of the through hole and a second layer

formed inside the first layer.

4. A semiconductor device according to claim 1, wherein the thickness of the sidewall is smallest on the substrate side and becomes gradually large as the sidewall moves away from the substrate.

5. A semiconductor device according to claim 1, wherein the first and second conductive layers serve as interconnections.

6. A semiconductor device according to claim 1, wherein the first and second conductive layers is made of aluminum.

7. A semiconductor device according to claim 1, wherein the first and second insulator layers is made of silicon oxide.

8. A semiconductor device according to claim 3, wherein the sidewall includes the first layer is formed of silicon nitride and the second layer is formed of silicon oxide.